

ABSTRACT OF THE DISCLOSURE

A phase change memory includes a plurality of word lines, a plurality of bit lines intersecting the word lines, and a plurality of memory cells arranged in rows along the word lines and located at corresponding intersection regions of the word lines and bit lines. Each of the memory cells includes a cell transistor having a gate connected to a corresponding word line, and a resistor and a phase change cell connected in series between a drain of the cell transistor and a corresponding bit line. In order to increase a cell drive current, the phase change memory also includes a plurality of auxiliary transistors respectively connected between the drains of the cell transistors of adjacent said memory cells.